BUK98180-100A/CUX-VB Datasheet

N-Channel 100-V (D-S) MOSFET

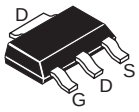
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
100	0.100 at V_{GS} = 10 V	5.0
	0.120 at V_{GS} = 4.5 V	4.5

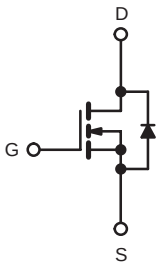
FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- Trench Power MOSFETs
- 175 °C Maximum Junction Temperature
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT

SOT-223





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**10 s**	**Steady State**	**Unit**
Drain-Source Voltage		V_{DS}	100		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T_J = 175 °C)[a]	T_A = 25 °C	I_D	5.0	4.5	A
	T_A = 70 °C		3.5	3.0	
Pulsed Drain Current		I_{DM}	25		
Avalanche Current		I_{AS}	15		
Single Pulse Avalanche Energy		E_{AS}	11		mJ
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	3.3	1.7	W
	T_A = 70 °C		2.3	1.2	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175		°C

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient [a]	t ≤ 10 s	R_{thJA}	36	45	°C/W
	Steady State		75	90	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	17	20	

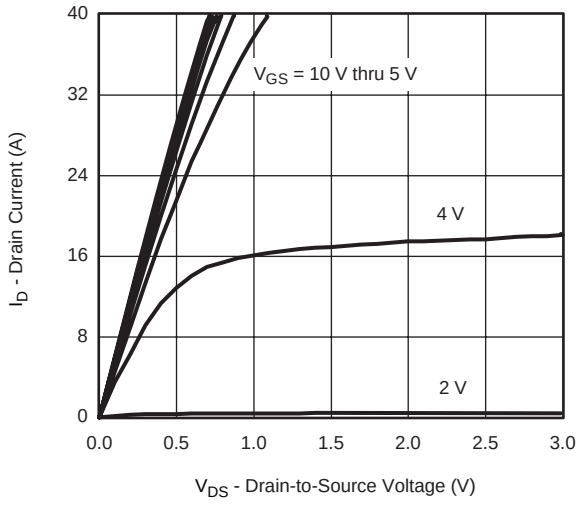
Notes:
a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	100			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	1.5		3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 100 V, V_{GS} = 0 V			1	µA
		V_{DS} = 100 V, V_{GS} = 0 V, T_J = 55 °C			20	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 5 V, V_{GS} = 10 V	40			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 6.0 A		0.110		Ω
		V_{GS} = 10 V, I_D = 4.0 A, T_J = 125 °C		0.122		
		V_{GS} = 10 V, I_D = 4.0 A, T_J = 175 °C		0.140		
		V_{GS} = 4.5 V, I_D = 3.1 A		0.120		
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 4.0 A		25		S
Diode Forward Voltage[a]	V_{SD}	I_S = 1.7 A, V_{GS} = 0 V		0.8	1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 50 V, V_{GS} = 10 V, I_D = 4.0 A		18	27	nC
Gate-Source Charge	Q_{gs}			3.4		
Gate-Drain Charge	Q_{gd}			5.3		
Gate Resistance	R_g	V_{GS} = 0.1 V, f = 5 MHz	0.5	1.4	2.4	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 50 V, R_L = 30 Ω I_D ≅ 1 A, V_{GEN} = 10 V, R_g = 6 Ω		10	20	ns
Rise Time	t_r			10	20	
Turn-Off Delay Time	$t_{d(off)}$			25	50	
Fall Time	t_f			12	24	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = 1.7 A, dI/dt = 100 A/µs		50	80	

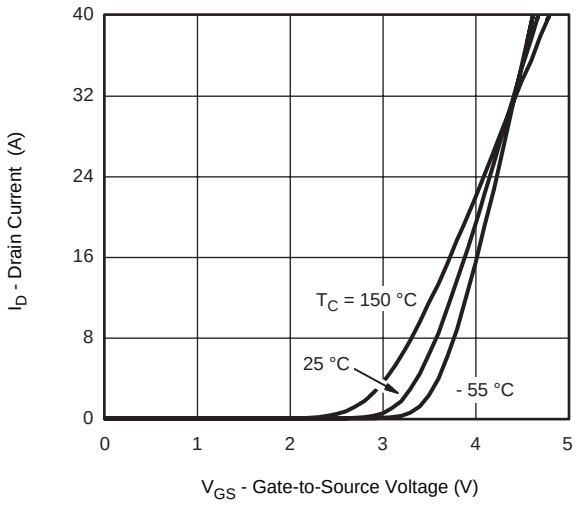
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

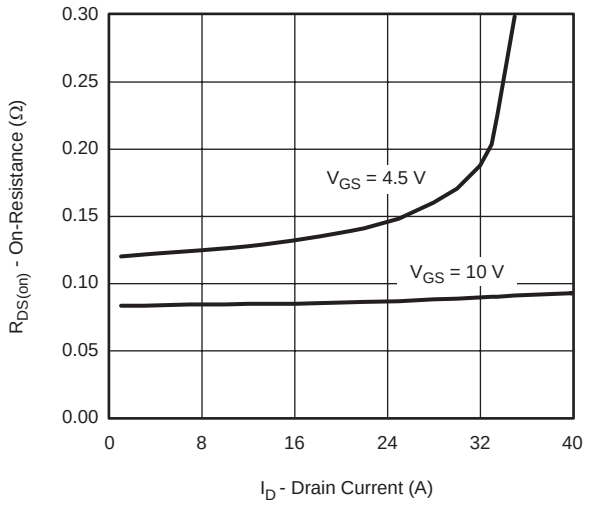


Output Characteristics

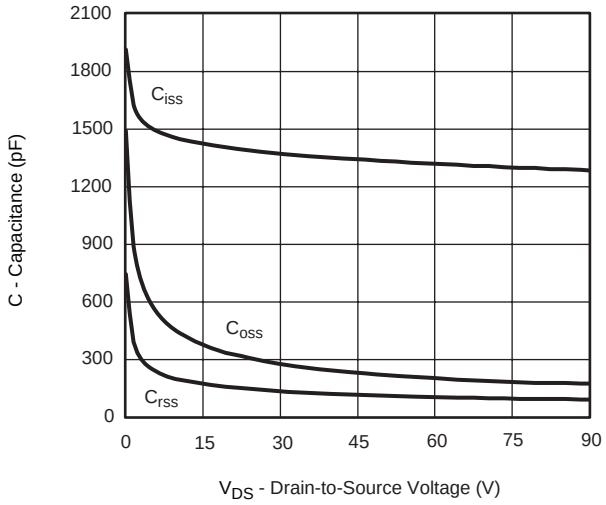


Transfer Characteristics

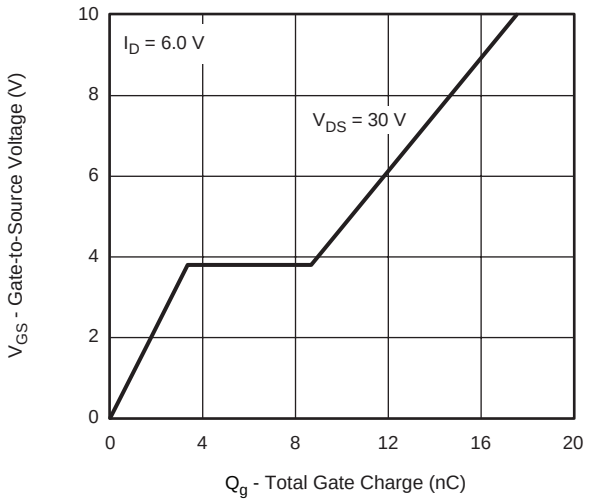
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



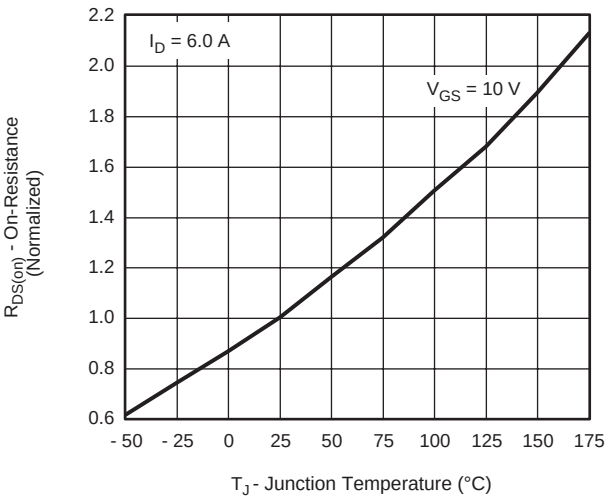
On-Resistance vs. Drain Current



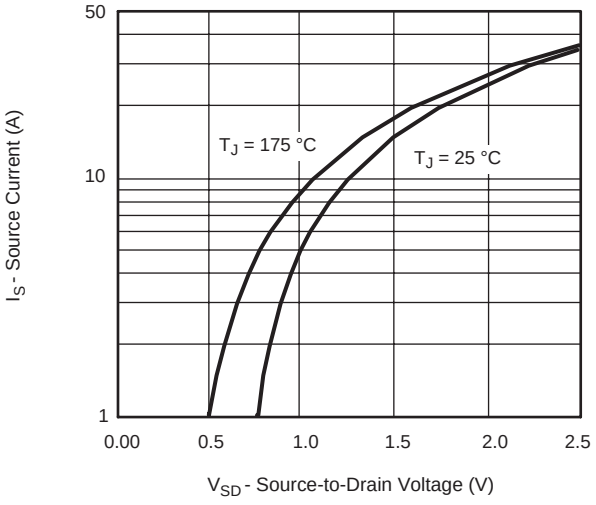
Capacitance



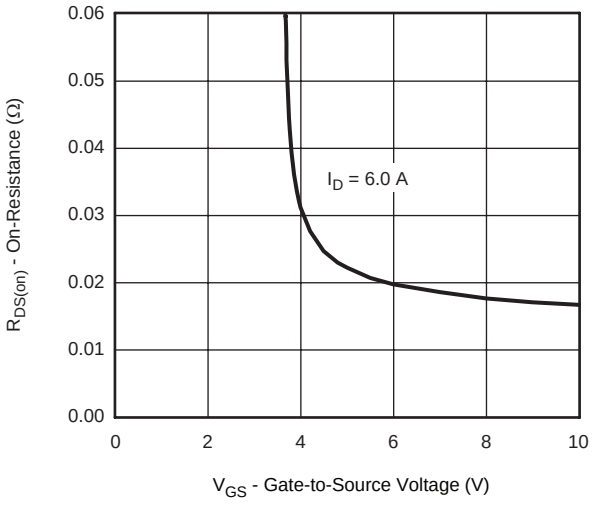
Gate Charge



On-Resistance vs. Junction Temperature

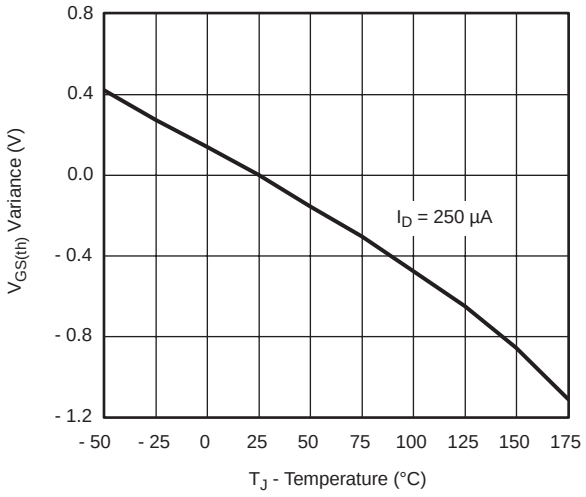


Source-Drain Diode Forward Voltage

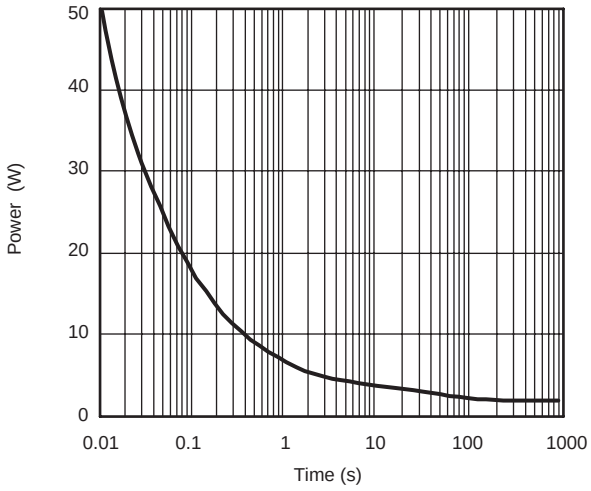


On-Resistance vs. Gate-to-Source Voltage

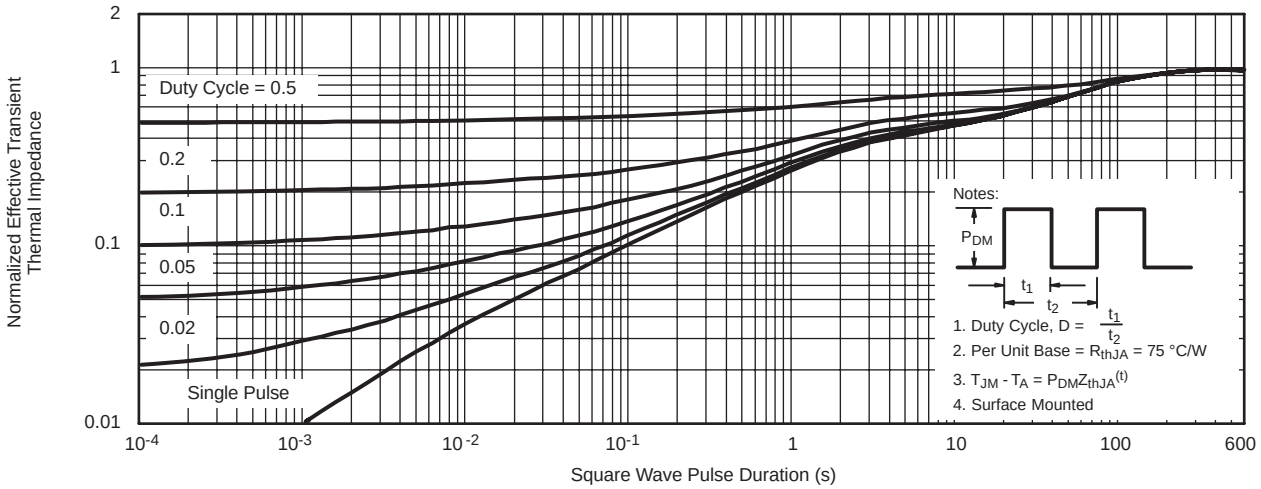
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



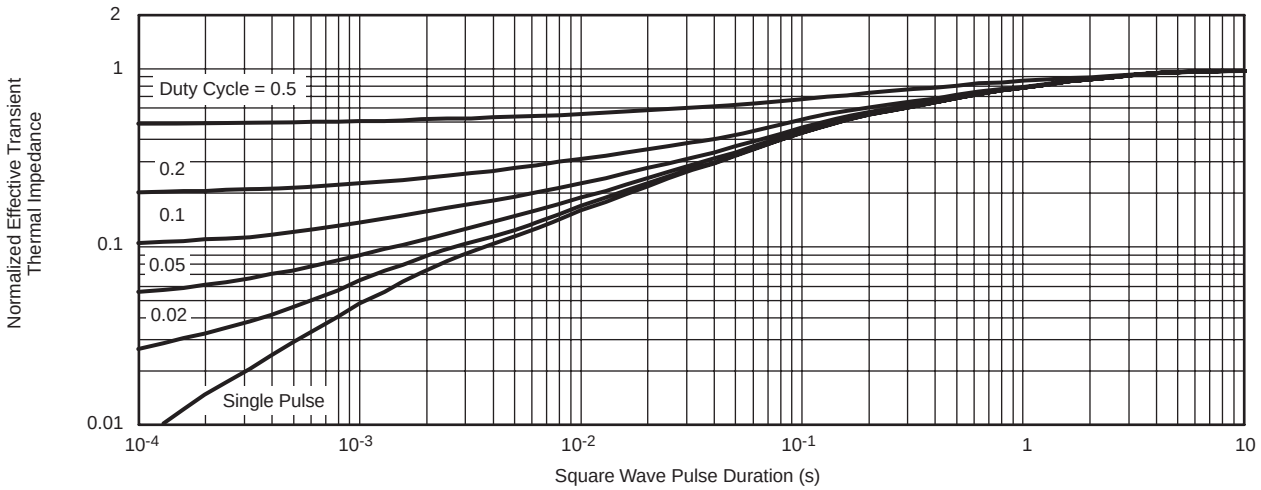
Threshold Voltage



Single Pulse Power

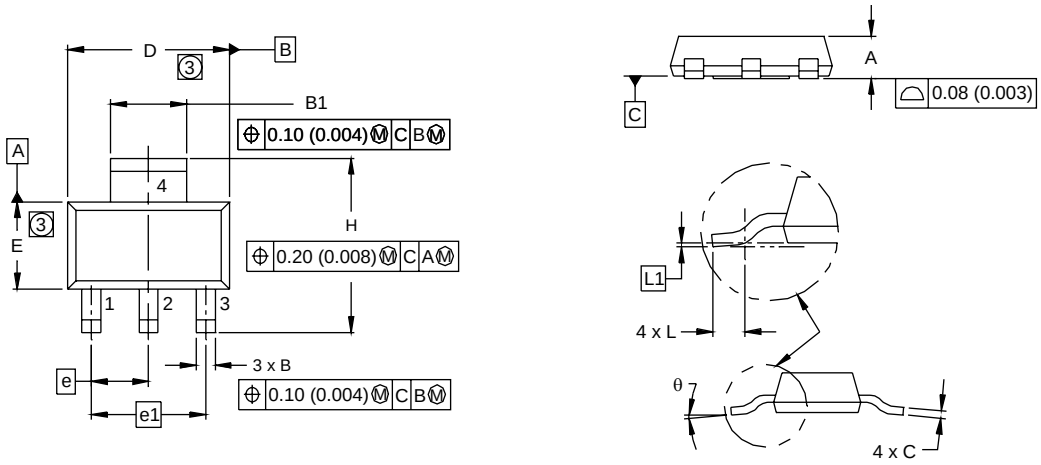


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

SOT-223 (HIGH VOLTAGE)



	MILLIMETERS		INCHES	
DIM.	**MIN.**	**MAX.**	**MIN.**	**MAX.**
A	1.55	1.80	0.061	0.071
B	0.65	0.85	0.026	0.033
B1	2.95	3.15	0.116	0.124
C	0.25	0.35	0.010	0.014
D	6.30	6.70	0.248	0.264
E	3.30	3.70	0.130	0.146
e	2.30 BSC		0.0905 BSC	
e1	4.60 BSC		0.181 BSC	
H	6.71	7.29	0.264	0.287
L	0.91	-	0.036	-
L1	0.061 BSC		0.0024 BSC	
θ	-	10'	-	10'
ECN: S-82109-Rev. A, 15-Sep-08 DWG: 5969				

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension do not include mold flash.
4. Outline conforms to JEDEC outline TO-261AA.

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